

V_{WM}=5V, 2pF ESD Protection Diode

FEATURES

• Meet IEC61000-4-2(ESD) ±15kV(air), ±8kV(contact)

Working Voltage: 5V

• Moisture sensitivity level: level 1, per J-STD-020

RoHS Compliant

• Halogen-free according to IEC 61249-2-21

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• High Speed Data Lines: USB 2.0 / VGA/ DVI /SDI

Notebooks, Desktops and Servers

Touch Panel

MECHANICAL DA	TA

Case: DFN1006L

• Molding compound meets UL 94 V-0 flammability rating

• Terminal: Matte tin plated leads, solderable per J-STD-002

• Meet JESD 201 class 1A whisker test

Polarity: As marked

• Weight: 0.742 mg (approximately)

KEY PARAMETERS					
PARAMETER	VALUE	UNIT			
P _{PPSM}	100	W			
I _{PP}	3	Α			
V _{WM}	5	V			
$V_{(BR)}$ at I_R = 1 mA	6	V			
V _C at I _{PP} = 3 A	15	V			
Package	DFN1006L				
Configuration	Single die				







ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)						
PARAMETER	SYMBOL	TESD5V0L1UC	UNIT			
Marking code on the device		ВН				
Rated random recurring peak Impulse power dissipation (tp=8/20µs waveform)	P _{PPSM}	100	W			
Peak impulse current (tp=8/20µs waveform)	I _{PP}	3	Α			
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	V _{ESD}	±15 ±8	kV			
Junction temperature range	T _J	-55 to +150	°C			
Storage temperature range	T _{STG}	-55 to +150	°C			



TESD5V0L1UC Taiwan Semiconductor

ELECTRICAL SPECIFICATIONS (T _A = 25°C unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	МАХ	UNIT
Reverse breakdown voltage (1)	I _R = 1 mA	$V_{(BR)}$	6	-	9.8	V
Rated working standoff voltage		V_{WM}	-	-	5	V
Reverse current (1)	V _R = 5 V	I _R	-	-	0.1	μΑ
Clamping voltage (2)	I _{PP} = 1 A	V _C	-	-	10	V
Clamping voltage (2)	I _{PP} = 3 A	V _C	-	-	15	V
Junction capacitance	f = 1 MHz, V _R = 0V	Сл	-	-	2	pF

Notes:

- 1. Pulse test with PW=30 ms
- 2. tp=8/20µs waveform

ORDERING INFORMATION						
ORDERING CODE	PACKAGE	PACKING				
TESD5V0L1UC RJG	DFN1006L	5K / 7" Reel				



CHARACTERISTICS CURVES

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

Fig.1 8/20µs pulse waveform

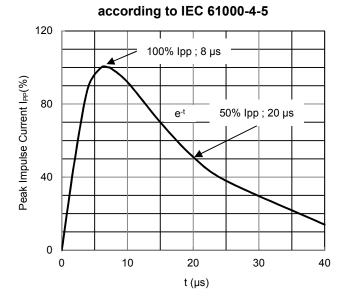


Fig.2 ESD pulse waveform according to IEC 6100-4-2

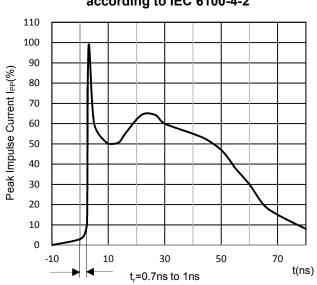


Fig.3 TLP I-V Curve

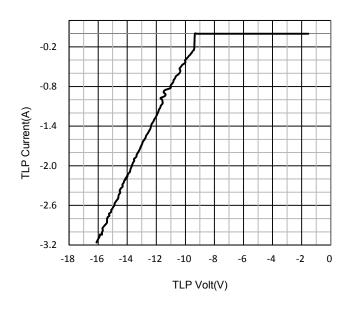
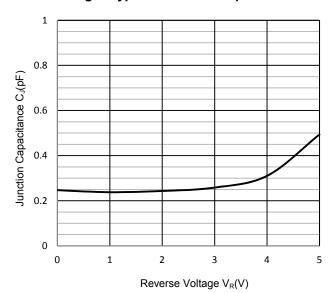


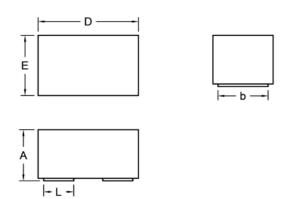
Fig.4 Typical Junction Capacitance





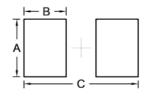
PACKAGE OUTLINE DIMENSION

DFN1006L



DIM.	Unit	(mm)	Unit (inch)		
Dilvi.	Min.	Max.	Min.	Max.	
Α	0.46	0.51	0.018	0.020	
b	0.50 (TYP.)		0.020 (TYP.)		
D	0.95	1.05	0.037	0.041	
E	0.55	0.65	0.022	0.026	
L	0.30 (TYP.)		0.012 (TYP.)		

SUGGESTED PAD LAYOUT



Symbol	Unit (mm)	Unit (inch)
Α	0.56	0.022
В	0.41	0.016
С	1.11	0.044



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